L	Hits	Search Text	DB	Time stamp
Number				2004/02/00
1	312	(Sic or silicon carbide) same (acetylene or "c.sub.2H.sub.4") same (silane)	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/03/02 14:47
2	130	(Sic or silicon carbide) same (acetylene or "c.sub.2H.sub.4") near10 (silane)	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/03/02 14:47
*			DERWENT; IBM_TDB	
3	60	(Sic or silicon carbide) near10 (acetylene or "c.sub.2H.sub.4") near10 (silane)	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/03/02 14:48
4	19	(Sic or silicon near2 carbide) near10 (acetylene or "c.sub.2H.sub.4") near10 (silane)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/03/02 15:45
5	11	"1162326"	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/03/02 15:45
6	4	"01162326"	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/03/02 16:16
7	178	(kuniaki near2 yagi or hiroyuki near2 nagasawa).in.	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/03/02 16:16
8	43	((kuniaki near2 yagi or hiroyuki near2 nagasawa).in.) and (sic or silicon adj carbide)	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/03/02 16:17
-	674	(sic or silicon adj carbide) same surface near2 react\$4	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/02/24 10:32
_	539	(sic or silicon adj carbide) near10 surface near2 react\$4	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/02/24 10:32
-	115	((sic or silicon adj carbide) near10 surface near2 react\$4) same (si or silicon adj substrate)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/02/24 10:34
_	45	((sic or silicon adj carbide) near10 surface near2 react\$4) near10 (sic or silicon adj carbide) near4 (layer or film) same (si or silicon adj substrate)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/02/24 11:09
-	1169	(sic or silicon adj carbide) near4 (layer or film) and temperature near4 rate	IBM_TDB USPAT; US-PGPUB;	2004/02/24 11:10
. –	135	(sic or silicon adj carbide) near4 (layer or film) same (heat\$3 or temperature) near4 rate	EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/02/24 11:11

Search History 3/2/04 4:20:54 PM

-	5	(sic or silicon adj carbide) near4 (layer	USPAT;	2004/02/24
		or film) same (heat\$3 or temperature) near4 rate same rapid	US-PGPUB; EPO; JPO;	11:34
		Tion I Late Same Lapid	DERWENT;	
			IBM_TDB	
-	191		USPAT;	2004/02/24
		or film) and (heat\$3 or temperature) near4 rate near10 grow\$5	US-PGPUB; EPO; JPO;	11:36
		Hear Frace Hear of Grows	DERWENT;	
			IBM TDB	
-	31		USPAT;	2004/02/24
		or film) and (heat\$3 or temperature)	US-PGPUB; EPO; JPO;	11:38
		near4 rate near10 grow\$5 same (sic or silicon adj carbide)	DERWENT;	
		Silicon adj carbide,	IBM TDB	
-	223		USPAT;	2004/02/24
		or film) and (heat\$3 or temperature)	US-PGPUB;	11:39
		near2 rate same (sic or silicon adj	EPO; JPO; DERWENT;	
		Carbide)	IBM TDB	
_	8	(sic or silicon adj carbide) near4 (layer	USPAT;	2004/02/24
	}	or film) and (heat\$3 or temperature)	US-PGPUB;	11:40
1		near2 rate same growth near2 temperature	EPO; JPO;	
		same (sic or silicon adj carbide)	DERWENT; IBM TDB	
-	12	(sic or silicon adj carbide) near4 (layer	USPAT;	2004/02/24
		or film) and (heat\$3 or temperature)	US-PGPUB;	11:44
		near2 rate near5 (ramp\$4 or elevat\$4)	EPO; JPO;	
		same (sic or silicon adj carbide)	DERWENT;	
	39	(heat\$3 or temperature) near2 rate near5	IBM_TDB USPAT;	2004/02/24
İ		(ramp\$4 or elevat\$4) same (sic or silicon	US-PGPUB;	11:46
	ļ	adj carbide)	EPO; JPO;	
			DERWENT;	
_	27	((heat\$3 or temperature) near2 rate near5	IBM_TDB USPAT;	2004/02/24
	"	(ramp\$4 or elevat\$4) same (sic or silicon	US-PGPUB;	11:44
		adj carbide)) not ((sic or silicon adj	EPO; JPO;	
		carbide) near4 (layer or film) and	DERWENT;	
		(heat\$3 or temperature) near2 rate near5 (ramp\$4 or elevat\$4) same (sic or silicon	IBM_TDB	İ
		(lamps of elevats) same (sic of silicon adj carbide))		
_	61	(heat\$3) near2 rate same growth near2	USPAT;	2004/02/24
		temperature	US-PGPUB;	11:46
			EPO; JPO; DERWENT;	
			IBM TDB	
_	7	(heat\$3) near2 rate same growth near2	USPAT;	2004/02/24
		temperature same (sic or silicon adj	US-PGPUB;	11:47
		carbide)	EPO; JPO;	
			DERWENT; IBM TDB	
-	474	(heat\$3) near2 rate same (sic or silicon	USPAT;	2004/02/24
		adj carbide)	US-PGPUB;	11:47
			EPO; JPO;	
			DERWENT;	
_	34	(heat\$3) near2 rate same (sic or silicon	<pre>IBM_TDB USPAT;</pre>	2004/02/24
		adj carbide) near3 (film or layer)	US-PGPUB;	11:53
		<u> </u>	EPO; JPO;	[
			DERWENT;	
_	29	"150" near5 rate same (sic or silicon adj	<pre>IBM_TDB USPAT;</pre>	2004/02/24
	-	carbide) near3 (film or layer)	US-PGPUB;	11:55
			EPO; JPO;	
			DERWENT;	
_	215	(\$3minute or \$3min) near5 rate same (sic	<pre>IBM_TDB USPAT;</pre>	2004/02/24
	213	or silicon adj carbide) near3 (film or	US-PGPUB;	14:13
		layer)	EPO; JPO;	
			DERWENT;	
			IBM_TDB	

-	8	(\$3minute or \$3min) near5 rate near5	USPAT;	2004/02/24
		(heat\$4) same (sic or silicon adj	US-PGPUB;	14:16
	1	carbide) near3 (film or layer)	EPO; JPO;	
	ł		DERWENT;	
			IBM_TDB	
-	51		USPAT;	2004/02/24
		adj carbide) near3 (film or layer)	US-PGPUB;	14:31
			EPO; JPO;	
	4		DERWENT;	
			IBM_TDB	2224/22/24
-	66	rate near3 (temperature) same (sic or	USPAT;	2004/02/24
		silicon adj carbide) near3 (film or	US-PGPUB; EPO; JPO;	14:35
		layer)	DERWENT;	
			IBM TDB	
_	221	rapid near2 thermal same heat\$4 near2	USPAT;	2004/02/24
	221	rate	US-PGPUB;	14:36
		lace	EPO; JPO;	14.50
			DERWENT;	
			IBM TDB	
l	2	rapid near2 thermal same heat\$4 near2	USPAT;	2004/02/24
	_	rate same susceptor	US-PGPUB;	14:37
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	24	rapid near2 thermal same heat\$4 near2	USPAT;	2004/02/24
1		rate same product\$	US-PGPUB;	14:56
1			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	31	rapid near2 thermal same heat\$4 near2	USPAT;	2004/02/24
1		rate same (deposit\$ or grow\$3)	US-PGPUB;	15:29
			EPO; JPO;	
			DERWENT;	
İ			IBM_TDB	
-	J 77	rapid near2 thermal near20 (sic or	USPAT;	2004/02/24
		silicon adj carbide)	US-PGPUB;	15:29
			EPO; JPO;	
	İ		DERWENT;	
l _	31	rapid near2 thermal near20 (sic or	IBM_TDB USPAT;	2004/02/24
	31	silicon adj carbide) near4 (layer or	US-PGPUB;	15:29
		film)	EPO; JPO;	15.25
		111m/	DERWENT;	
	1		IBM TDB	
_	67	(silicon or si) near2 substrate and (RTP	USPAT;	2004/03/01
!		or rapid adj thermal near2 process\$5)	US-PGPUB;	15:46
		near3 rate	EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	3	(sic or silicon adj carbide) near2 (film	USPĀT;	2004/03/01
		or layer) and (RTP or rapid adj thermal	US-PGPUB;	15:48
		near2 process\$5) near3 rate	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	4		USPAT;	2004/03/01
		rapid adj thermal near2 process\$5) near3	US-PGPUB;	15:48
		rate	EPO; JPO;	
			DERWENT;	
		/	IBM_TDB	2004/02/01
_	673	(sic or silicon adj carbide) same (heat\$3	USPAT;	2004/03/01
		or ramp\$4 or elevat\$4) near5 rate	US-PGPUB;	15:50
			EPO; JPO;	
			DERWENT;	
_	50	 (sic or silicon adj carbide) same (heat\$3	IBM_TDB USPAT;	2004/03/01
ĺ		or ramp\$4 or elevat\$4) near5 rate near10	US-PGPUB;	15:53
		(rapid\$3 or fast\$3)	EPO; JPO;	
		, <u>r</u> = -,	DERWENT;	
			IBM TDB	

	2	4855254.pn.	USPAT;	2004/03/01
-	-	10002011	US-PGPUB;	16:00
	1		EPO; JPO;	
	,		DERWENT;	
			IBM_TDB	
	2	reactor same rapid near2 thermal near10	USPAT;	2004/03/01
		rate same substrate	US-PGPUB;	16:01
			EPO; JPO;	.
			DERWENT;	
			IBM_TDB	2004/03/01
_	16	reactor same rapid near2 thermal near10	USPAT;	2004/03/01
		rate	US-PGPUB;	16:24
			EPO; JPO;	
			DERWENT;	
		0.1	IBM_TDB USPAT;	2004/03/01
-	23	tungsten near2 halogen near2 lamp near10		16:26
	1	(rate)	US-PGPUB; EPO; JPO;	10.20
1			DERWENT;	
			IBM TDB	
1	1		1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1	